$\Phi$
TAIWAN SEMICONDUCTOR

## Pb <br> RoHS <br> COMPLIANCE



## Features

UL Recognized File \# E-326243
$\diamond \quad$ Glass passivated chip junction.
$\star$ High efficiency, Low VF
« High current capability
« High reliability

- High surge current capability
\& Low power loss
$\diamond$ Green compound with suffix "G" on packing code \& prefix " G " on datecode.


## Mechanical Data

$\diamond$ Cases: TO-220AB molded plastic
\& Epoxy: UL 94V-0 rate flame retardant
< Terminals: Pure tin plated, lead free. solderable per MIL-STD-202, Method 208 guaranteed
$\diamond$ Polarity: As marked
» High temperature soldering guaranteed: $260^{\circ} \mathrm{C} / 10$ seconds $.16^{\prime \prime},(4.06 \mathrm{~mm})$ from case.
> Weight: 2.24 grams

GP1001 - GP1007
10.0 AMPS. Glass Passivated Rectifiers

TO-220AB


Dimensions in inches and (millimeters)


Marking Diagram
GP100X = Specific Device Code
$\mathrm{G} \quad=$ Green Compound
Y $\quad=$ Year
WW = Work Week

## Maximum Ratings and Electrical Characteristics

Rating at $25^{\circ} \mathrm{C}$ ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz , resistive or inductive load.
For capacitive load, derate current by $20 \%$

| Type Number | Symbol | $\begin{gathered} \text { GP } \\ 1001 \end{gathered}$ | $\begin{gathered} \text { GP } \\ 1002 \end{gathered}$ | $\begin{gathered} \text { GP } \\ 1003 \end{gathered}$ | $\begin{gathered} \text { GP } \\ 1004 \end{gathered}$ | $\begin{gathered} \text { GP } \\ 1005 \end{gathered}$ | $\begin{gathered} \text { GP } \\ 1006 \end{gathered}$ | $\begin{gathered} \text { GP } \\ 1007 \end{gathered}$ | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Maximum Recurrent Peak Reverse Voltage | VRRM | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| Maximum RMS Voltage | VRMS | 35 | 70 | 140 | 280 | 420 | 560 | 700 | V |
| Maximum DC Blocking Voltage | VDC | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| Maximum Average Forward RectifiedCurrent $375 "(9.5 \mathrm{~mm})$ Lead Length @ $T_{C}=100^{\circ} \mathrm{C}$ | IF(AV) | 10.0 |  |  |  |  |  |  | A |
| Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method) | IFSM | 125 |  |  |  |  |  |  | A |
| Maximum Instantaneous Forward Voltage @5.0A | VF | 1.1 |  |  |  |  |  |  | V |
| Maximum DC Reverse Current at @ $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ Rated DC Blocking Voltage (Note 1) @ $\mathrm{T}_{\mathrm{A}}=125^{\circ} \mathrm{C}$ | IR | $\begin{array}{r} 5.0 \\ 200 \\ \hline \end{array}$ |  |  |  |  |  |  | uA uA |
| Typical Junction Capacitance ( Note 3) | Cj | 30 |  |  |  |  |  |  | pF |
| Typical Thermal Resistance ( Note 2 ) | Rejc | 3.0 |  |  |  |  |  |  | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Operating and Storage Temperature Range | TJ, Tstg | -65 to +150 |  |  |  |  |  |  | ${ }^{\circ} \mathrm{C}$ |

Notes: 1. Pulse Test with PW=300 usec,1\% Duty Cycle
2. Mounted on Heatsink size 2 " $\times 3$ " $\times 0.25$ " Al-Plate.
3. Measured at 1 MHz and Applied Reverse Voltage of 4.0 Volts D.C.

## RATINGS AND CHARACTERISTIC CURVES (GP1001 THRU GP1007)




FIG.4- TYPICAL JUNCTION CAPACITANCE


FIG.2- TYPICAL REVERSE CHARACTERISTICS



